



#### 40V +175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BVDSS	Rds(ON) Max	I <sub>D</sub> Max Tc = +25°C
40V	$15m\Omega$ @ $V_{GS} = 10V$	42A

# **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power-management functions
- DC-DC converters

#### **Features and Benefits**

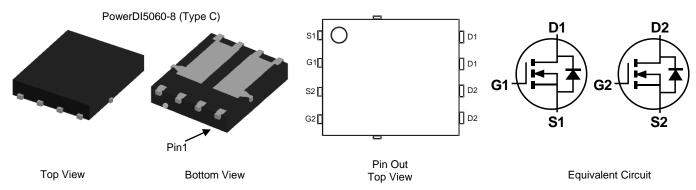
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH4011SPDQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

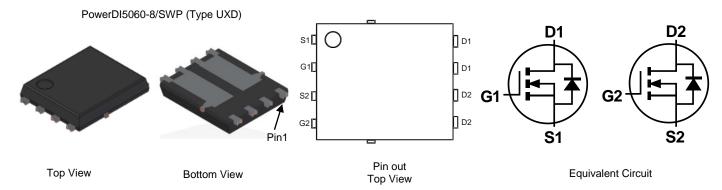
#### **Mechanical Data**

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

Site 1:



Site 2:



Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

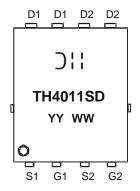


### Ordering Information (Note 4)

Part Number	Bookaga	Packing		
Part Number	Package	Qty.	Carrier	
DMTH4011SPDQ-13	PowerDI5060-8 (Type C)	2,500	Tape & Reel	
DMTH4011SPDQ-13	PowerDI5060-8/SWP (Type UXD)	2,500	Tape & Reel	

Note: 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



⊃¦¦ = Manufacturer's Marking TH4011SD = Product Type Marking Code YYWW = Date Code Marking YY or YY = Year (ex: 23 = 2023) WW = Week (01 to 53)

# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		VDSS	40	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	ID	42 29.7	А
Continuous Drain Current (Note 5) $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$		ID	11.1 7.8	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	IDM	70	А	
Maximum Continuous Body Diode Forward Current (Note 6)		Is	39.3	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		Isм	70	А
Avalanche Current, L = 0.3mH		las	11.9	А
Avalanche Energy, L = 0.3mH		Eas	21.4	mJ

# **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)		RθJA	57	°C/W
Total Power Dissipation (Note 6)	T <sub>C</sub> = +25°C	P <sub>D</sub>	37.5	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	4	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

otes: 5. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal bias to bottom layer 1inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).

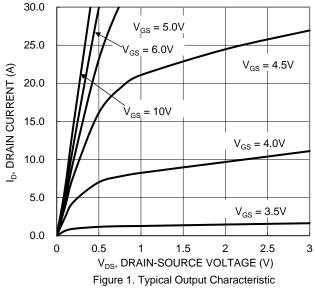


# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	40	1	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V <sub>DS</sub> = 32V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(th)	2		4	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	RDS(ON)		11.6	15	mΩ	$V_{GS} = 10V, I_{D} = 20A$	
Diode Forward Voltage	$V_{SD}$	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	1	805	_	pF	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	208	_	pF		
Reverse Transfer Capacitance	Crss	_	15	_	pF	-1 = 11VII 12	
Gate Resistance	Rg	_	2.76	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	10.6	_	nC	V 20V I 20A	
Gate-Source Charge	Q <sub>gs</sub>	_	2.2	_	nC	$V_{DS} = 20V, I_D = 20A,$	
Gate-Drain Charge	Qgd	_	2.7	_	nC	$V_{GS} = 10V$	
Turn-On Delay Time	tD(ON)	_	4.1	_	ns		
Turn-On Rise Time	tR	_	3.8	_	ns	V <sub>DD</sub> = 20V, V <sub>GS</sub> = 10V,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	8.6	_	ns	$R_G = 1.6\Omega, I_D = 20A$	
Turn-Off Fall Time	tF	_	1.9	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	10.2	_	ns	IF = 15A, di/dt = 400A/µs	
Body Diode Reverse Recovery Charge	QRR	_	9.6	_	nC		

7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing. Notes:





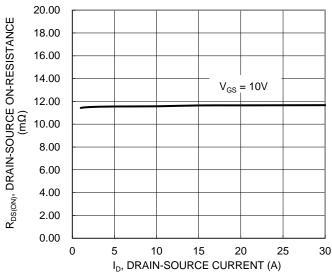


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

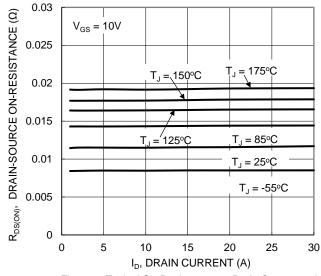


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

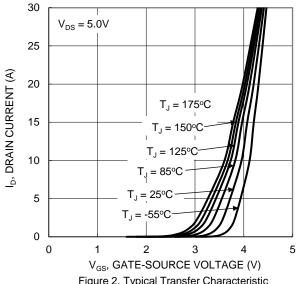


Figure 2. Typical Transfer Characteristic

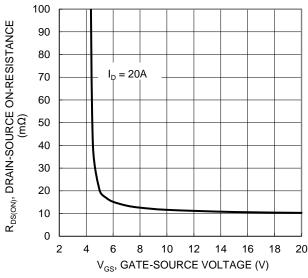


Figure 4. Typical Transfer Characteristic

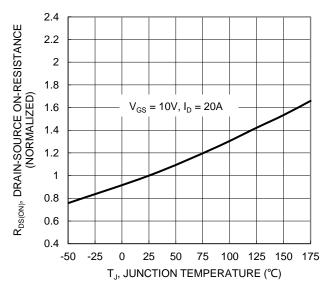


Figure 6. On-Resistance Variation with Temperature





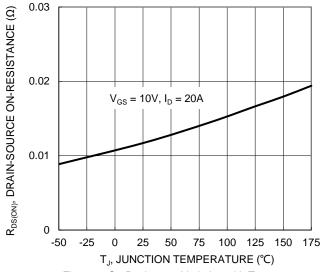
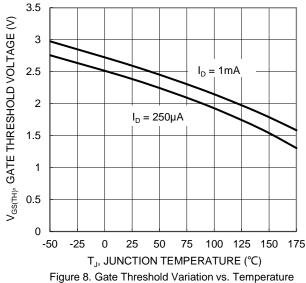


Figure 7. On-Resistance Variation with Temperature



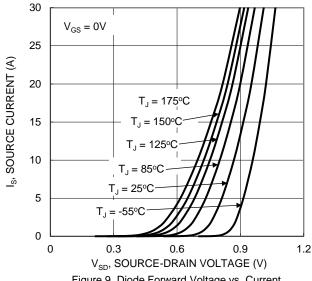
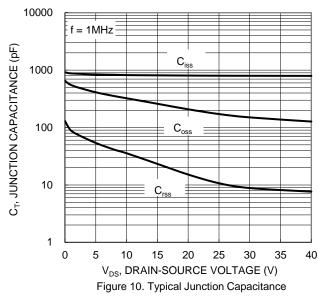
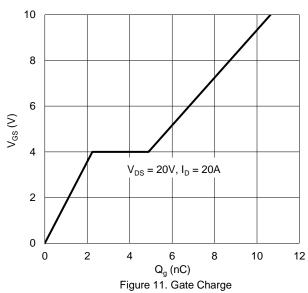


Figure 9. Diode Forward Voltage vs. Current





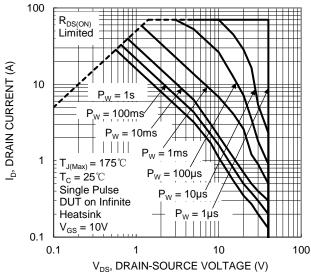


Figure 12. SOA, Safe Operation Area



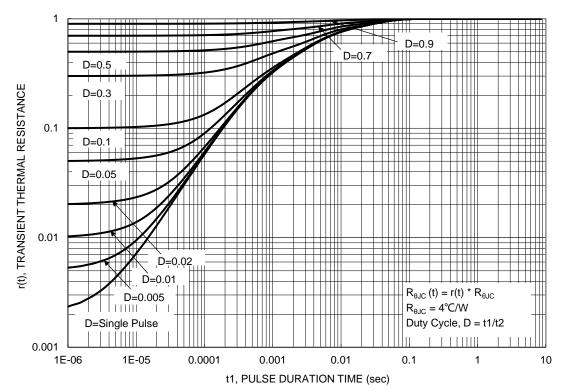


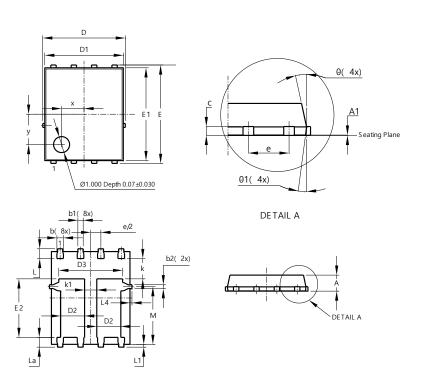
Figure 13. Transient Thermal Resistance



### **Package Outline Dimensions**

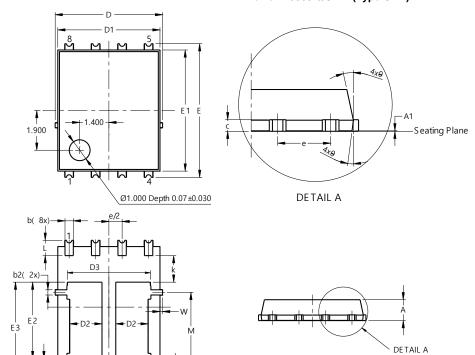
Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type C)



PowerDI5060-8 (Type C)			
Dim	Min	Max	Тур
Α	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
C	0.23	0.33	0.277
D	5	.15 BS0	С
D1	4.85	4.95	4.90
D2	1.40	1.60	1.50
D3	1	-	3.98
Е	6	.15 BS0	2
E1	5.75	5.85	5.80
E2	3.56	3.76	3.66
е	1	.27BS0	
k	-	-	1.27
k1	0.56	-	-
L	0.51	0.71	0.61
La	0.51	0.71	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
М	3.50	3.71	3.605
х	-	-	1.400
у	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

#### PowerDI5060-8/SWP (Type UXD)



PowerDI5060-8/SWP			
(Type UXD)			
Dim	Min	Max	Тур
Α	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	(	).25REF	
С	0.230	0.330	0.277
D	5	.15 BS0	2
D1	4.70	5.10	4.90
D2	1.46	1.66	1.55
D3	3.78	4.18	3.98
Е	6	.40 BS0	)
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
е	1	1.27BSC	)
k	1.05		
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
M	3.205	4.005	3.605
W	0.025	0.225	0.125
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

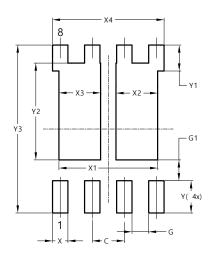
-b4( 8x)



# **Suggested Pad Layout**

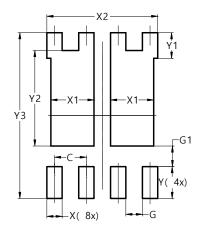
Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type C)



Dimensions	Value (in mm)
	(111 111111)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	3.910
X2	1.650
Х3	1.650
X4	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

### PowerDI5060-8/SWP (Type UXD)



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	1.720
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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